

N-Channel Enhancement Mode Power MOSFET**MTN7N60FP** **$BV_{DSS} : 650V @ T_j = 150^{\circ}C$** **$R_{DS(ON)} : 1.2 \Omega$** **$I_D : 7A$** **Description**

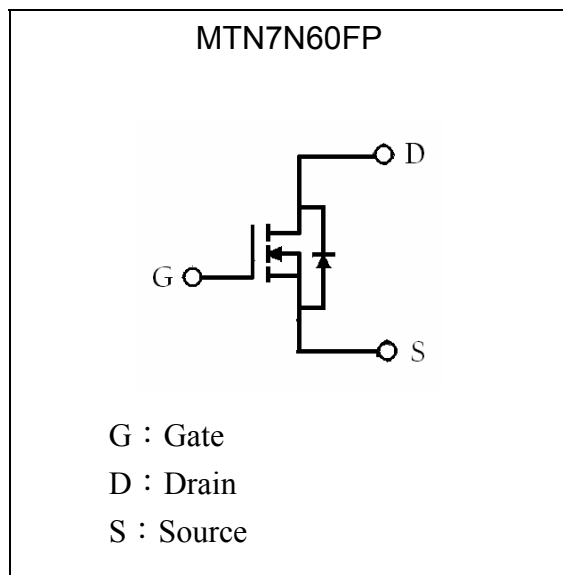
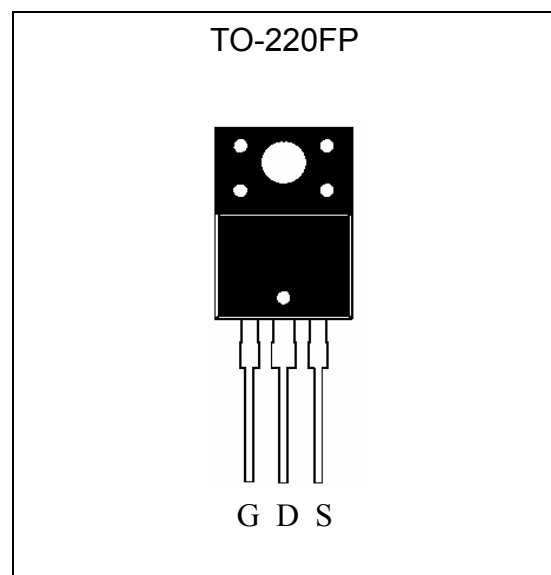
The MTN7N60FP is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220FP package is universally preferred for all commercial-industrial applications

Features

- $BV_{DSS} = 650V$ typically @ $T_j = 150^{\circ}C$
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

Applications

- Switching Mode Power Supply
- LCD Panel Power
- Adapter
- E-bike Charger

Symbol**Outline**

**Absolute Maximum Ratings** ($T_C=25^{\circ}\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	7*	A
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$	I_D	4.4*	A
Pulsed Drain Current @ $V_{GS}=10\text{V}$ (Note 1)	I_{DM}	21*	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	115	mJ
Avalanche Current (Note 1)	I_{AR}	7	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	3.1	mJ
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Maximum Temperature for Soldering @ Lead at 0.125 in(0.318mm) from case for 10 seconds	T_L	300	$^{\circ}\text{C}$
Maximum Temperature for Soldering @ Package Body for 10 seconds	T_{PKG}	260	$^{\circ}\text{C}$
Total Power Dissipation ($T_C=25^{\circ}\text{C}$) Linear Derating Factor	P_d	31	W
		0.25	W/ $^{\circ}\text{C}$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^{\circ}\text{C}$

*Drain current limited by maximum junction temperature

Note : 1.Repetitive rating; pulse width limited by maximum junction temperature.

2. $I_{AS} \leq 6\text{A}$, $V_{DD}=50\text{V}$, $L=7\text{mH}$, $V_G=10\text{V}$, starting $T_J=+25^{\circ}\text{C}$.3. $I_{SD} \leq 7\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J=+25^{\circ}\text{C}$.**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	4.0	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5	$^{\circ}\text{C}/\text{W}$

**Characteristics (Tc=25°C, unless otherwise specified)**

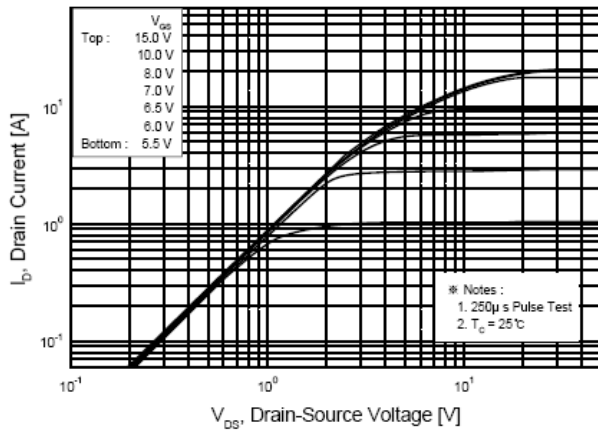
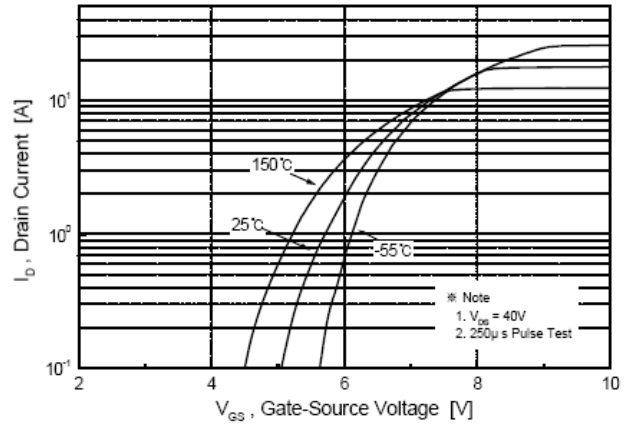
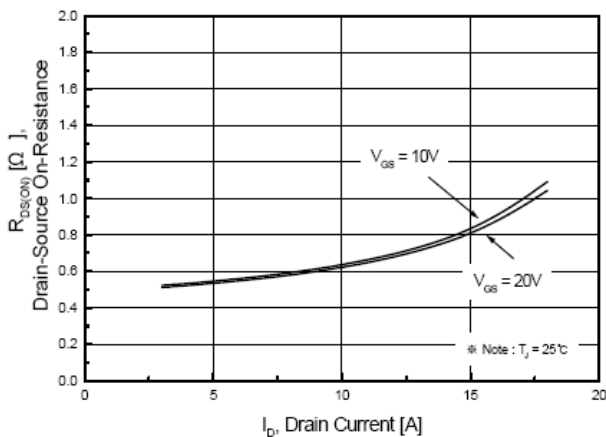
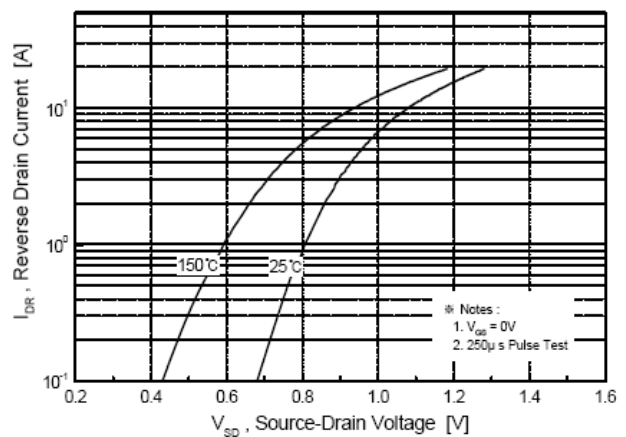
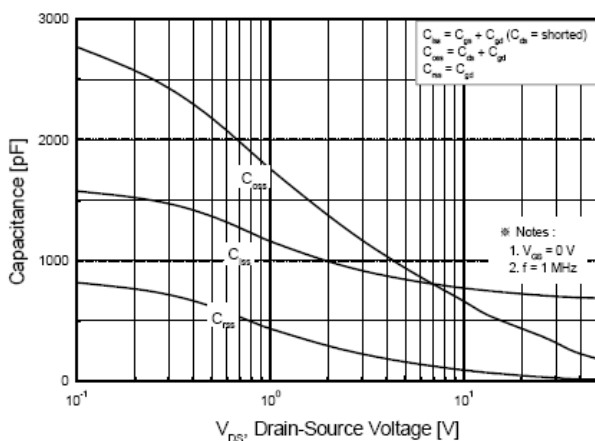
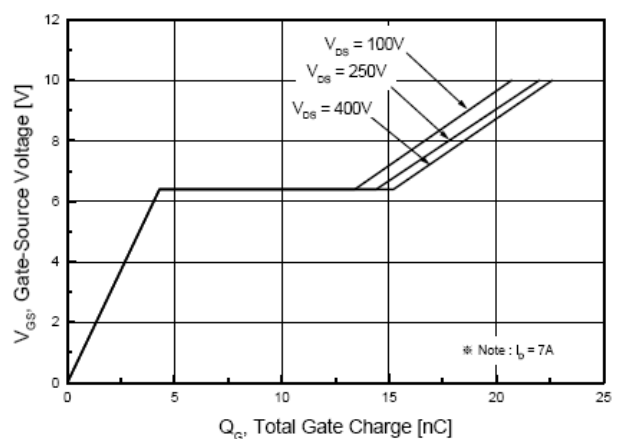
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	600	-	-	V	V _{GS} =0, I _D =250μA, T _j =25°C
BV _{DSS}	-	650	-	V	V _{GS} =0, I _D =250μA, T _j =150°C
ΔBV _{DSS} /ΔT _j	-	0.6	-	V/°C	Reference to 25°C, I _D =250μA
BV _{DS}	-	700	-	V	V _{GS} =0, I _D =7A
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	10	-	S	V _{DS} =15V, I _D =6A
I _{GSS}	-	-	±100	nA	V _{GS} =±30
I _{DSS}	-	-	1	μA	V _{DS} =600V, V _{GS} =0
	-	-	10	μA	V _{DS} =480V, V _{GS} =0, T _j =125°C
*R _{DS(ON)}	-	-	1.2	Ω	V _{GS} =10V, I _D =3.5A
Dynamic					
*Q _g	-	31.3	-	nC	I _D =6A, V _{DD} =300V, V _{GS} =10V
*Q _{gs}	-	6.9	-		
*Q _{gd}	-	14	-		
*t _{d(ON)}	-	14.2	-	ns	V _{DD} =300V, I _D =6A, V _{GS} =10V, R _G =10Ω, R _D =50Ω
*t _r	-	11.8	-		
*t _{d(OFF)}	-	40.1	-		
*t _f	-	18.8	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{iss}	-	1482	-		
C _{oss}	-	121.7	-		
C _{rss}	-	14	-		
Source-Drain Diode					
*V _{SD}	-	-	1.5	V	I _S =7A, V _{GS} =0V
*I _S	-	-	7	A	
*I _{SM}	-	-	21		
*t _{rr}	-	504.9	-	ns	V _{GS} =0, I _F =6A, dI/dt=100A/μs
*Q _{rr}	-	47.59	-	μC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Ordering Information

Device	Package	Shipping	Marking
MTN7N60FP	TO-220FP (RoHS compliant)	50 pcs/tube, 20 tubes/box, 4 boxes / carton	7N60

Characteristic Curves

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics

Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics


Characteristic Curves(Cont.)

Figure 7. Breakdown Voltage Variation vs. Temperature

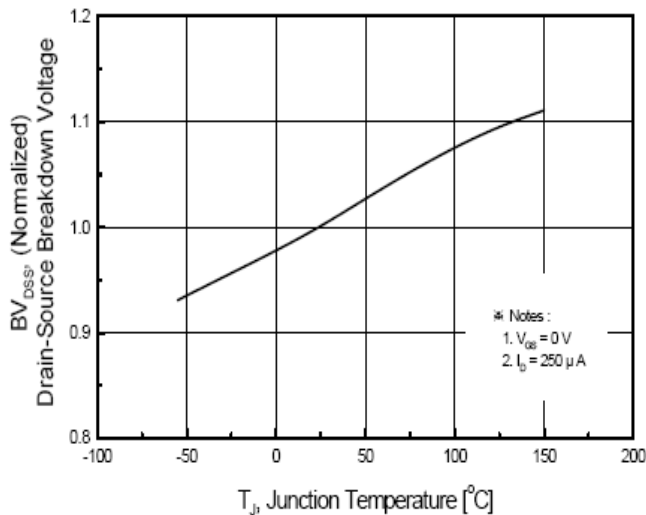


Figure 8. On-Resistance Variation vs. Temperature

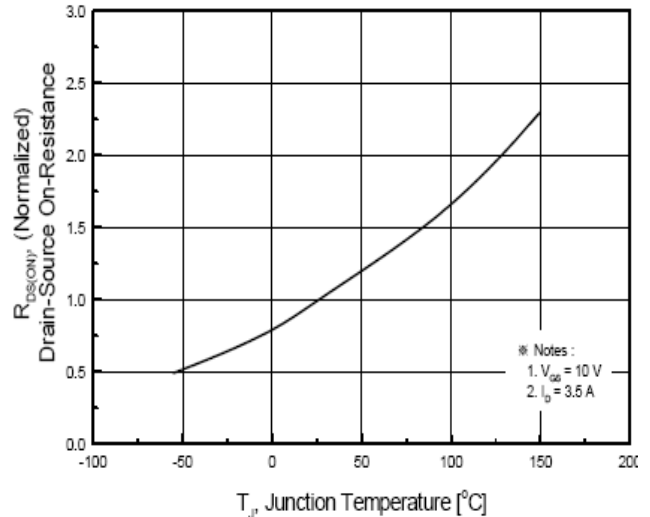


Figure 9 . Maximum Safe Operating Area

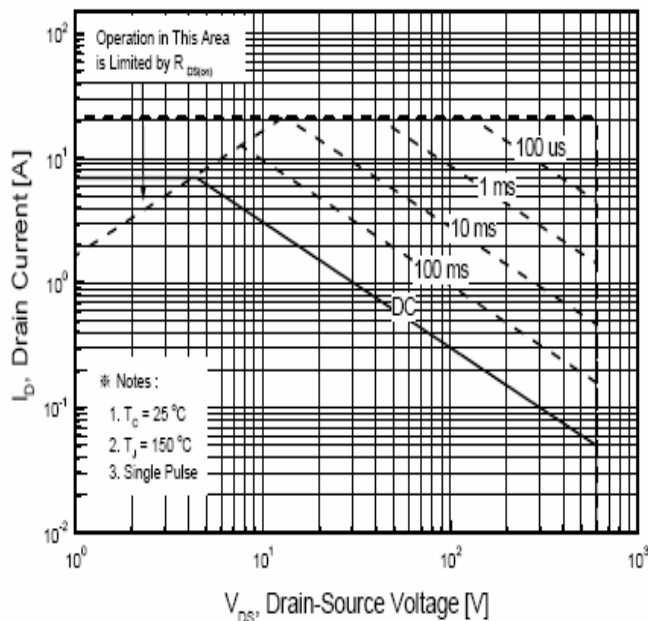


Figure 10. Maximum Drain Current vs. Case Temperature

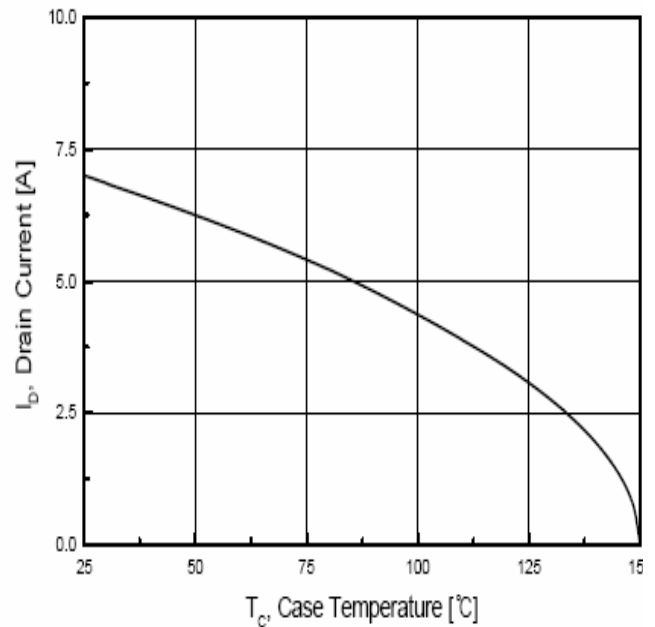
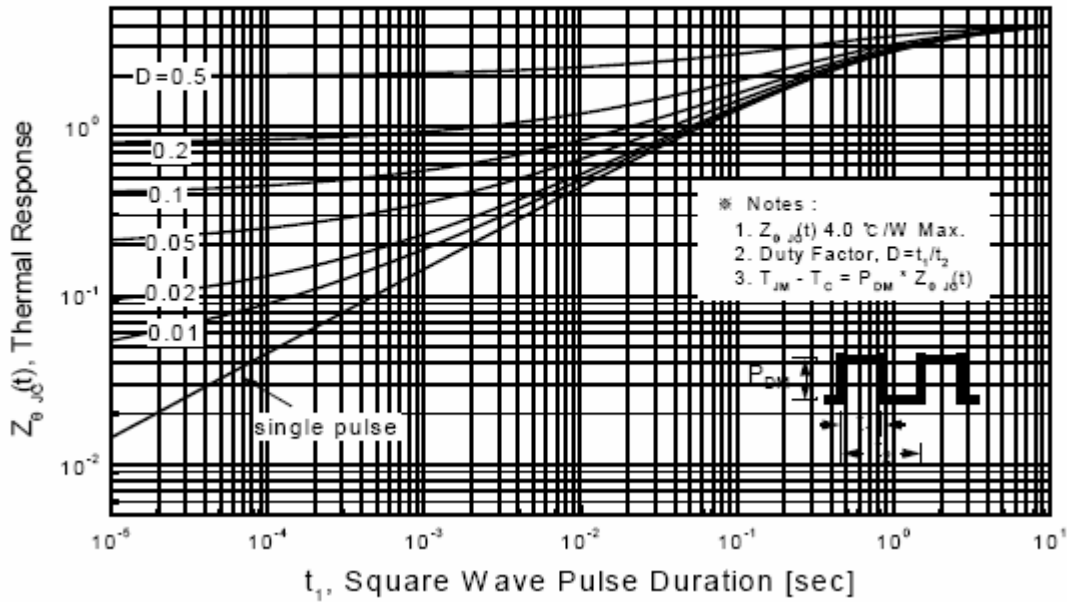
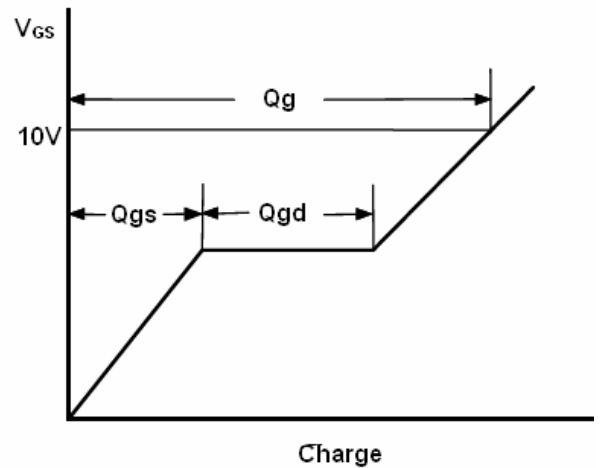
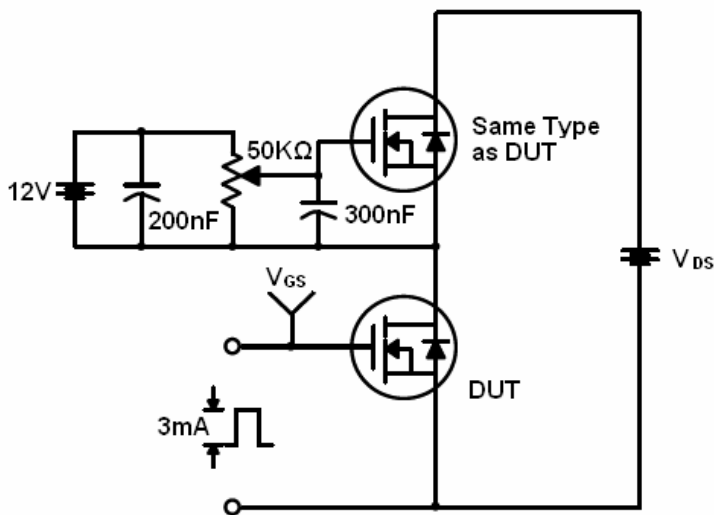
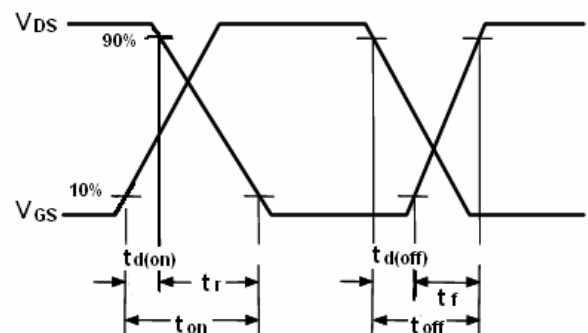
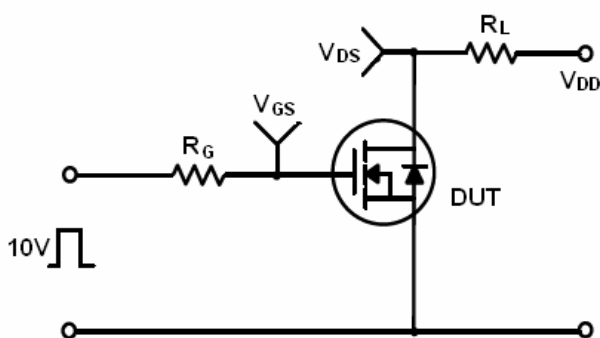
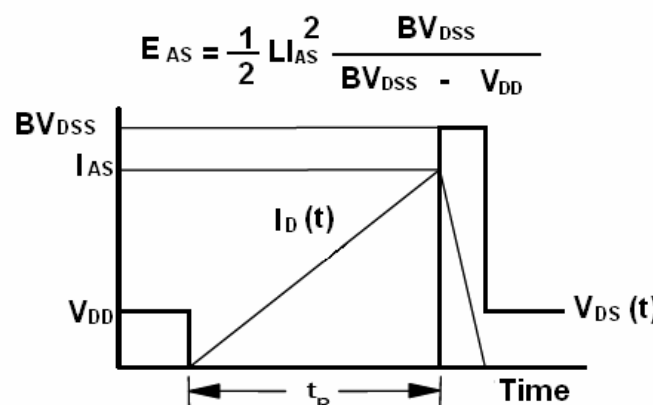
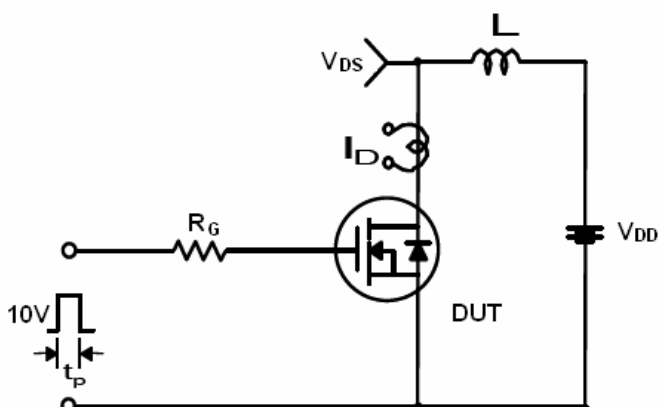


Figure 11. Transient Thermal Response Curve

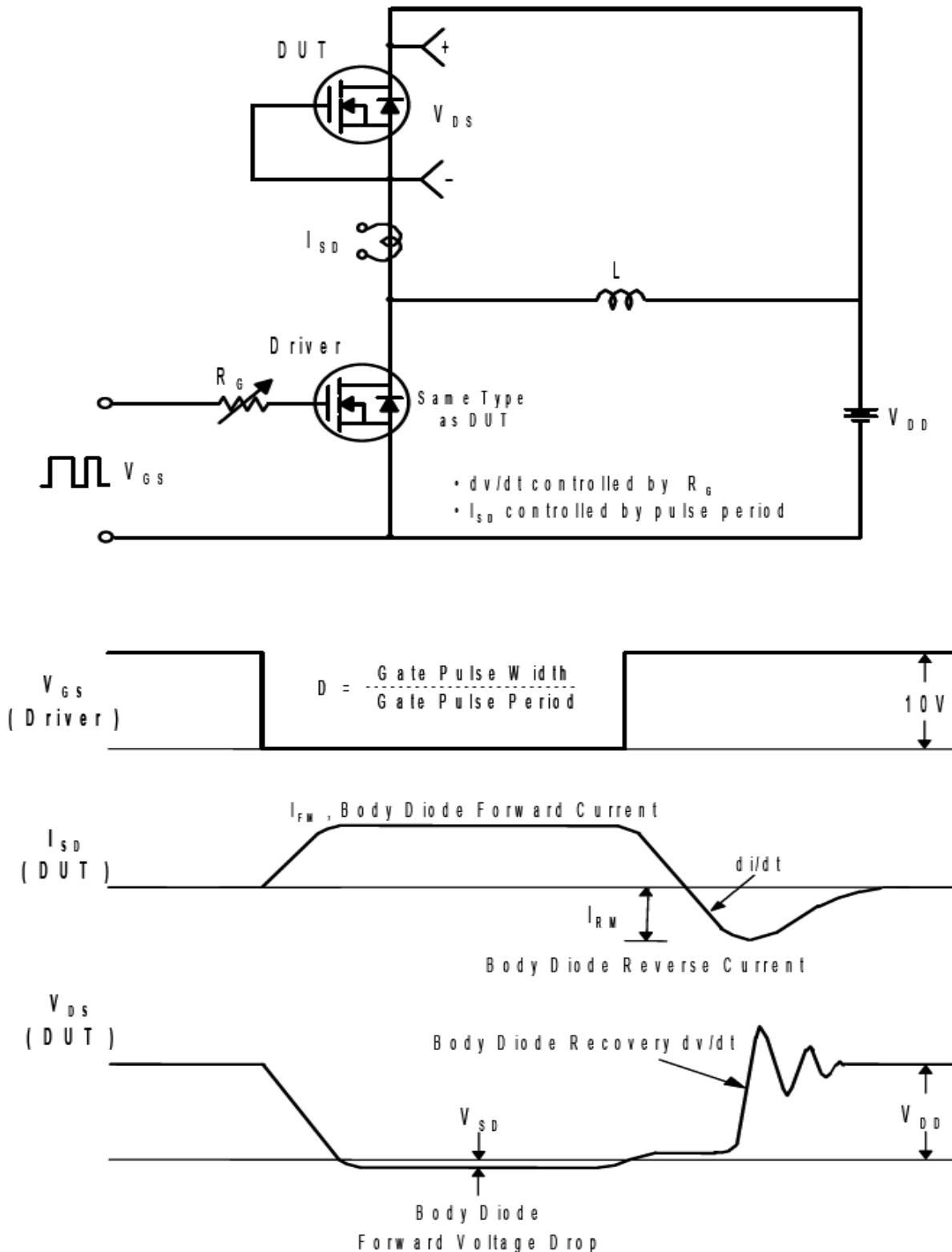


Test Circuit and Waveforms

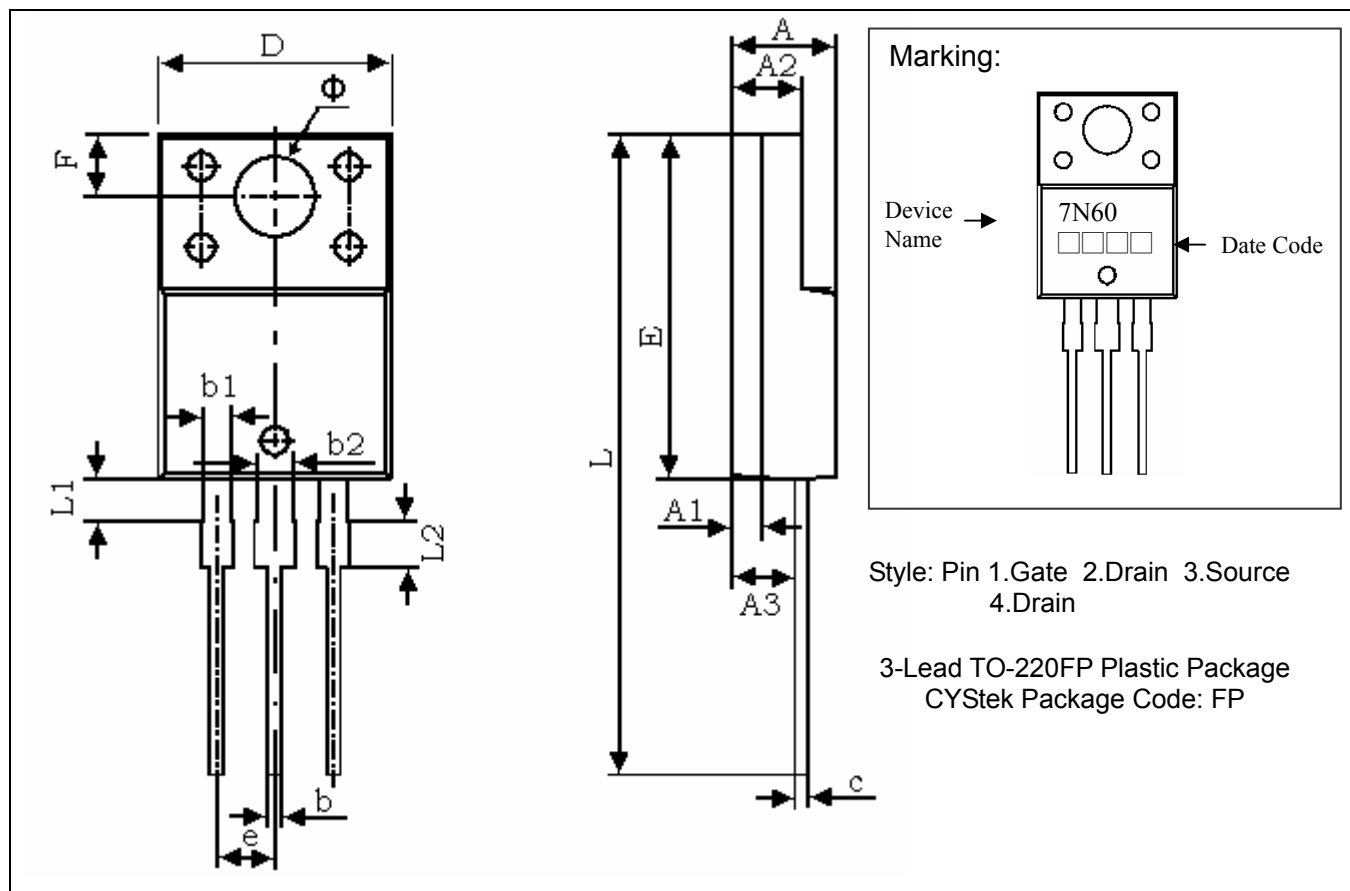
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching Test Circuit & Waveforms


Test Circuit and Waveforms(Cont.)

Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-220FP Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.169	0.185	4.300	4.700	D	0.392	0.408	9.960	10.360
A1	0.051 REF		1.300 REF		E	0.583	0.598	14.800	15.200
A2	0.110	0.126	2.800	3.200	e	0.100 TYP		2.540 TYP	
A3	0.098	0.114	2.500	2.900	F	0.106 REF		2.700 REF	
b	0.020	0.030	0.500	0.750	Φ	0.138 REF		3.500 REF	
b1	0.043	0.053	1.100	1.350	L	1.102	1.118	28.000	28.400
b2	0.059	0.069	1.500	1.750	L1	0.067	0.075	1.700	1.900
c	0.020	0.030	0.500	0.750	L2	0.075	0.083	1.900	2.100

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: KFC ; pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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